ELECTRONICS, INC.
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NTE525
Silicon Diode
High Voltage Fast Recovery Switch

Features:
- Fast Switching
- Low Leakage
- High Current Capability
- High Surge Capability
- High Reliability

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified, Note 1)

Maximum Recurrent Peak Reverse Voltage, V_{RRM} 2000V
Maximum RMS Voltage, V_{RMS} 1400V
Maximum DC Blocking Voltage, V_{DC} 2000V
Maximum Average Forward Rectified Current (T_A = +50°C, .375” Lead Length), I_O 200mA
Peak Forward Surge Current (8.3ms single half sine–wave superimposed), I_{FSM} 30A
Operating Junction Temperature Range, T_J . . . . . –65° to +175°C
Storage Temperature Range, T_{stg} . . . . . –65° to +175°C

Note 1. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Electrical Characteristics: (T_A = +25°C unless otherwise specified, Note 1)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	I_F = 0.5A/0.2A DC	–	–	4	V
Maximum DC Reverse Current	I_R	V_{DC} = 2000V	–	–	5	μA
Maximum Full Load Reverse Current Average	I_R	T_A = +55°C, .375” Lead Length	–	–	100	μA
Maximum Reverse Recovery Time	t_{rr}	I_F = 0.5A, I_R = 1A, I_{RR} = 0.25A	–	–	500	ns

Note 1. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

